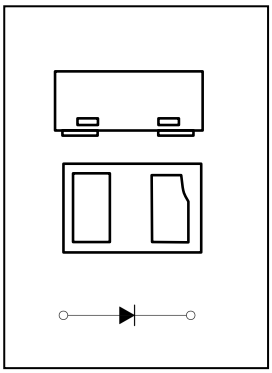
DFN1006-2L Plastic-Encapsulate Diodes

FEATURES

- Small Package
- Low Reverse Current
- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion



MARKING: T4

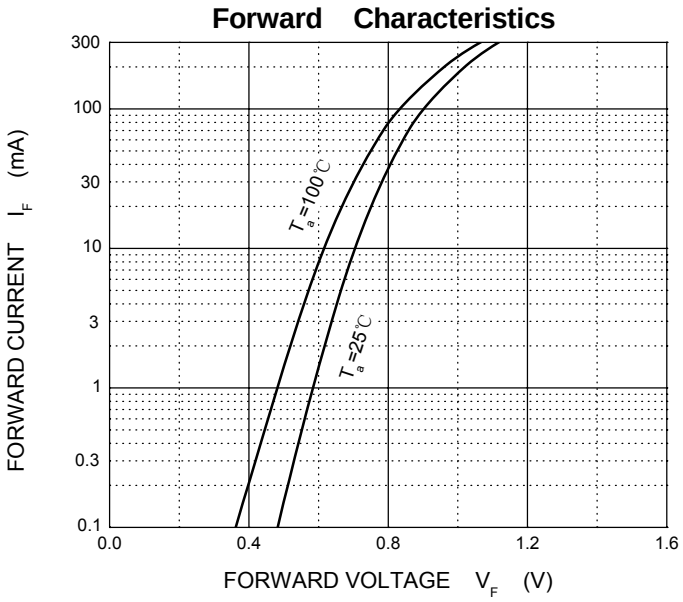
Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

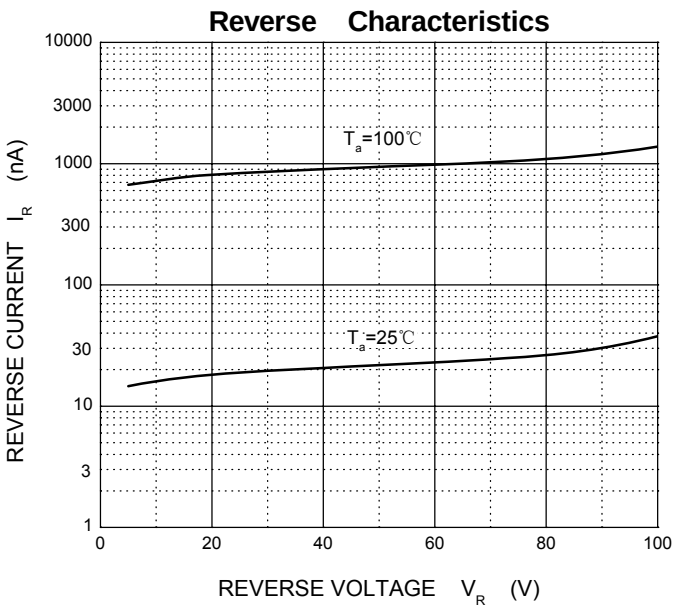
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	250	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	Pd	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	℃/W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

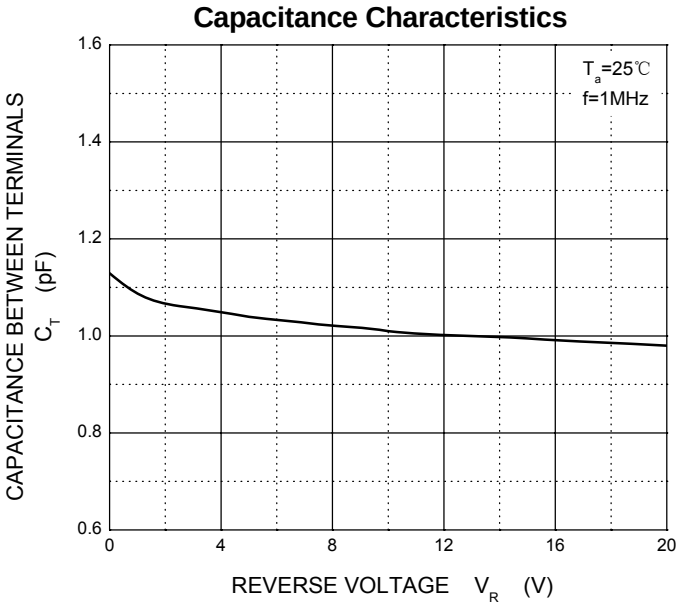
Electrical Ratings @Ta=25℃

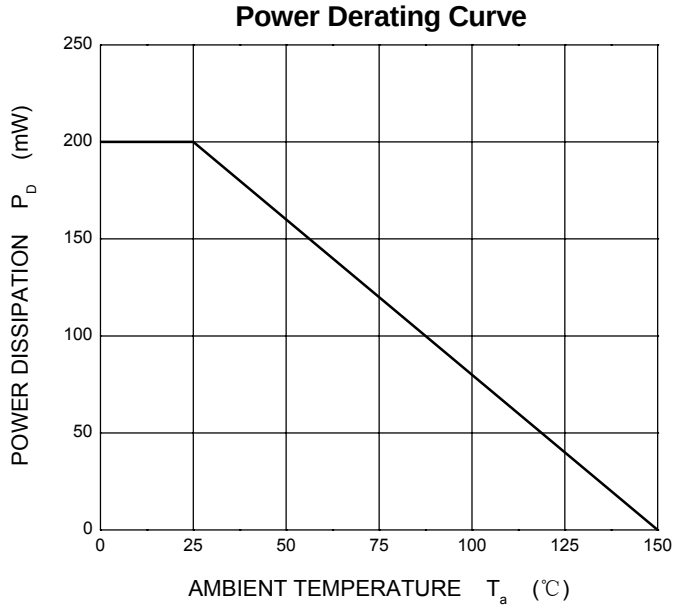
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	75			V	I_R=10μA
Forward Voltage	V_{F1}	0.62		0.72	V	I_F=5mA
	V_{F2}			0.855	V	I_F=10mA
	V_{F3}			1.0	V	I_F=100mA
	V_{F4}			1.25	V	I_F=150mA
Reverse Current	I_{R1}			2.5	μA	V_R=75V
	I_{R2}			25	nA	V_R=20V
Capacitance Between Terminals	C_T			4	pF	V_R=0V,f=1MHz
Reverse Recovery Time	t_{rr}			4	ns	I_F=I_R=10mA Irr=0.1XI_R,R_L=100Ω

Typical Characteristics

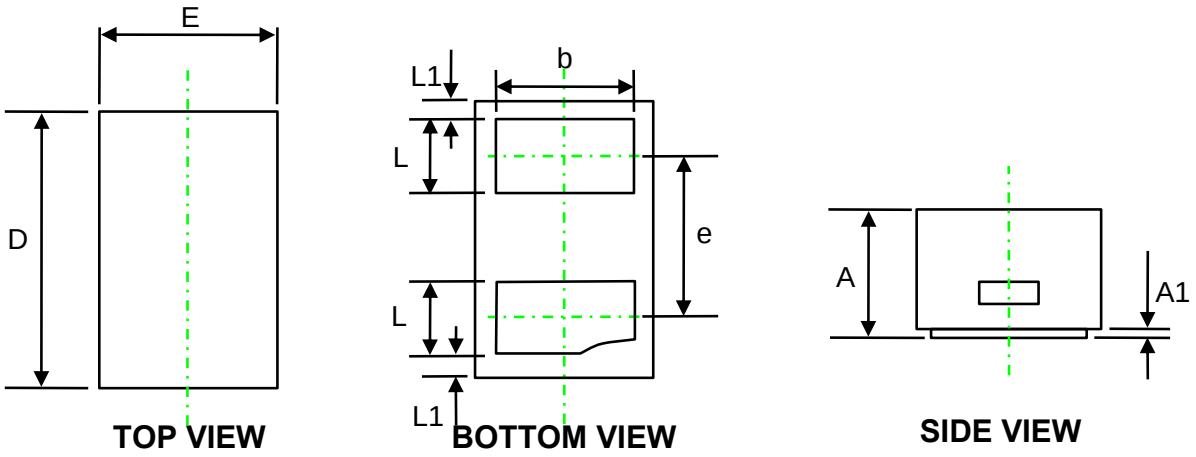






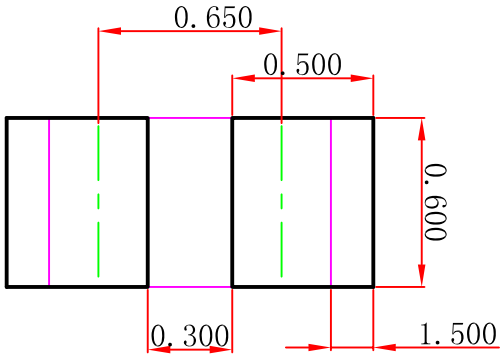


DFN1006-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters (mm)		
	Min.	Typ.	Max.
A	0.44	0.47	0.50
A1	0.00	0.03	0.05
D	0.95	1.00	1.08
E	0.55	0.60	0.68
b	0.40	0.50	0.60
e	-	0.65	-
L	0.20	0.25	0.30
L1	0.05 REF.		

DFNWB1.0× 0.6-02L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.050mm.
3.The pad layout is for reference purposes only.